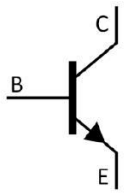
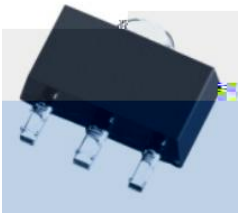
SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

, , 2SA1201

High $f_T$, high $V_{CEO}$, small flat package, complementary pair with 2SA1201.

Power amplifier applications.

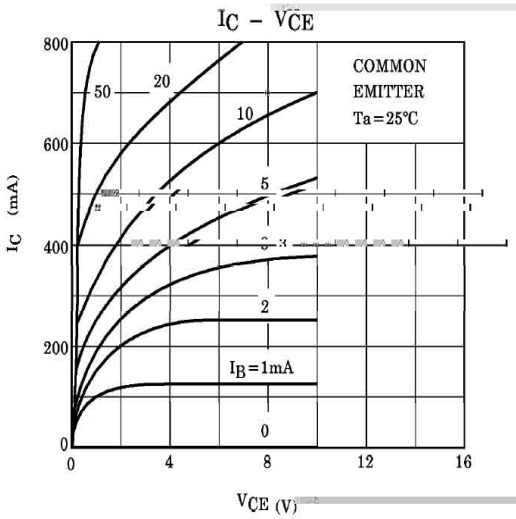


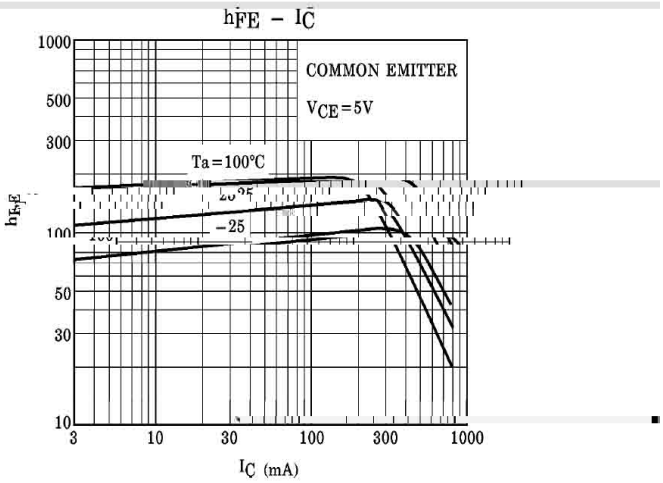



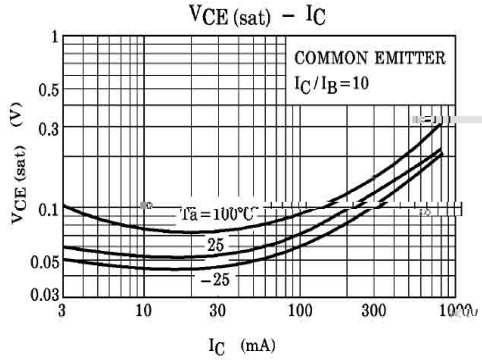
PIN1 Base PIN 2 Collector PIN 3 Emitter

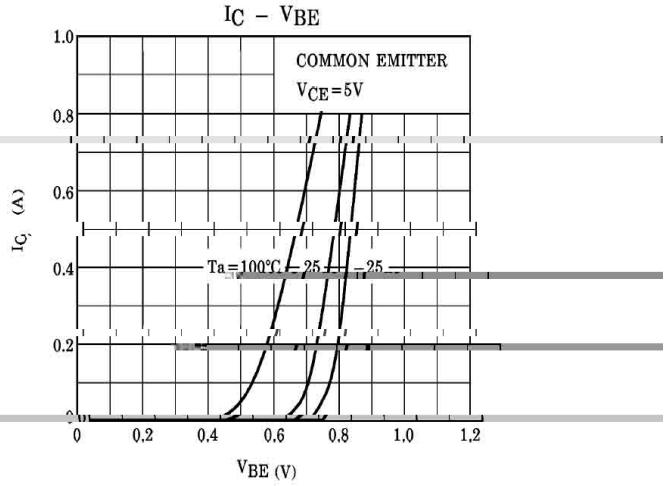
| $h_{FE}$ Classifications Symbol | O | Y |
|---|---|---|
| $h_{FE}$ Range | 80 160 | 120 240 |
| Marking | HCO ⁎⁎ | HCY ⁎⁎ |

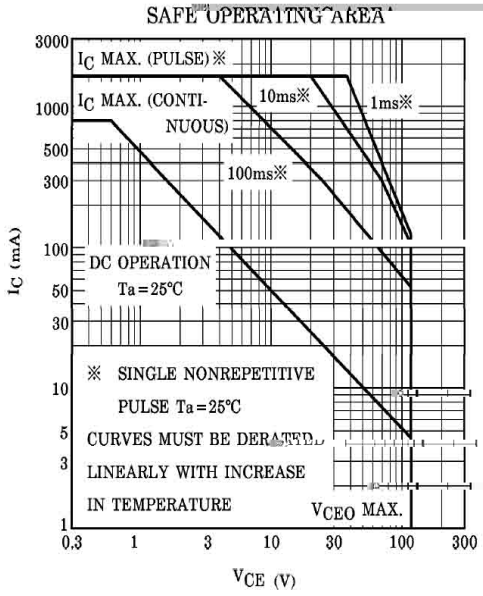
| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Collector to Base Voltage | $V_{CBO}$ | 120 | V |
| Collector to Emitter Voltage | $V_{CEO}$ | 120 | V |
| Emitter to Base Voltage | $V_{EBO}$ | 5.0 | V |
| Collector Current-Continuous | $I_C$ | 800 | mA |
| Collector Base-Continuous | $I_B$ | 160 | mA |
| Collector Power Dissipation | $P_C$ | 500 | mW |
| Collector Power Dissipation* | *$P_C$ | 1.0 | W |

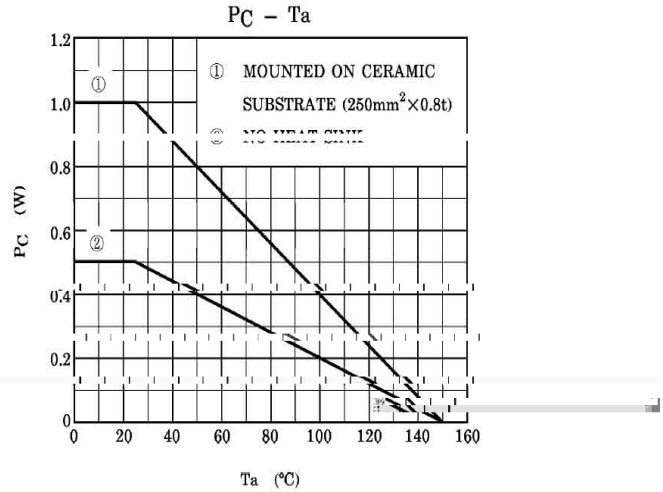

IC – VCE
COMMON EMITTER
Ta=25°C
50
20
10
5
2
IB=1mA
0
IC (mA)
VCE (V)

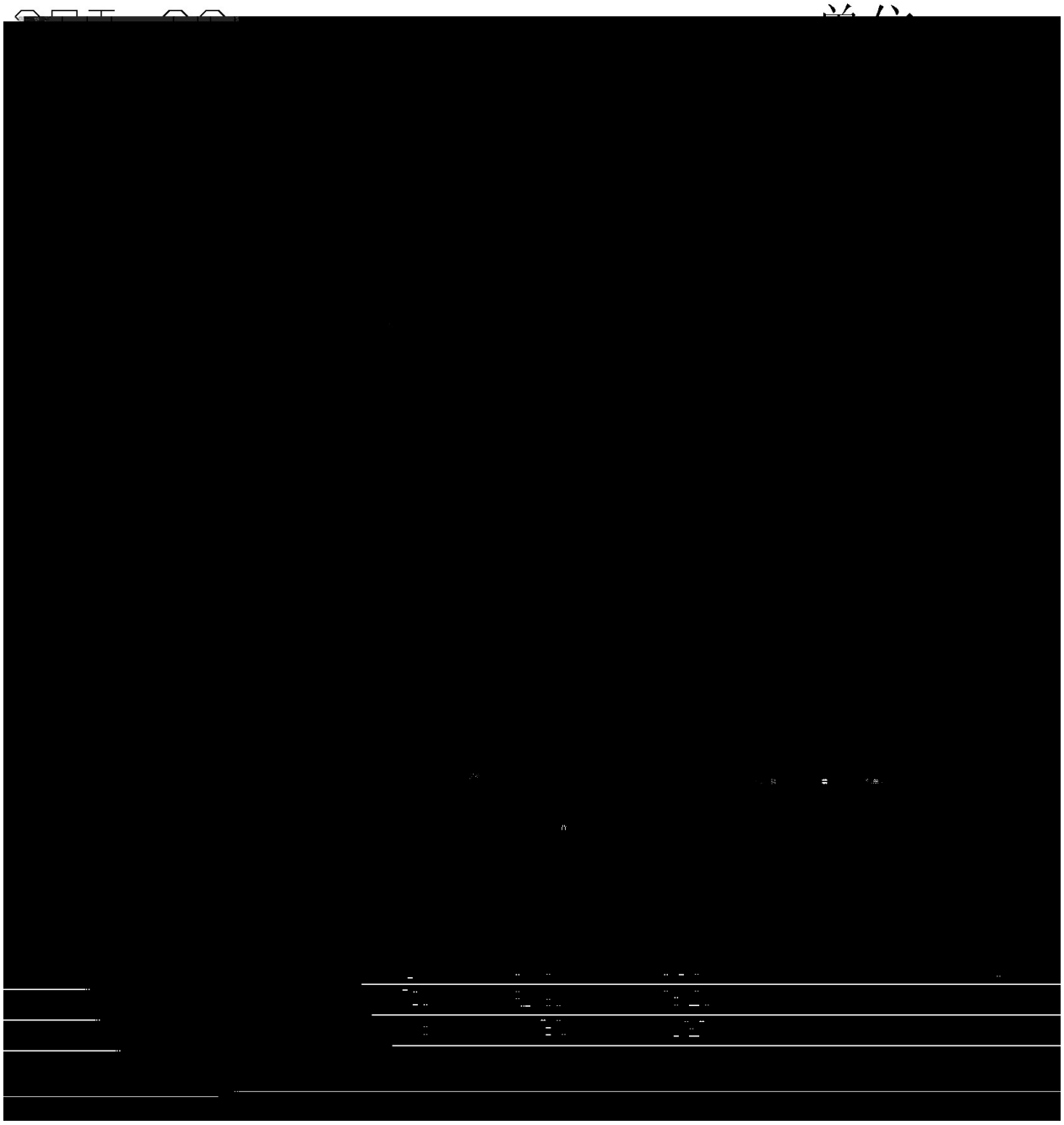

hFE – IC
COMMON EMITTER
VCE=5V
Ta=100°C
25
−25
hFE
IC (mA)

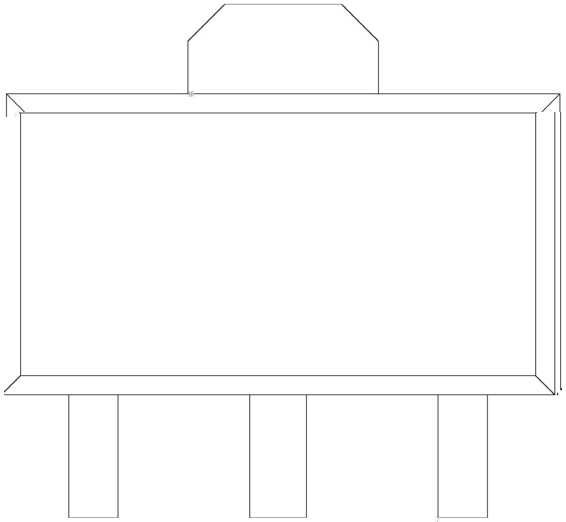

VCE (sat) – IC
COMMON EMITTER
IC/IB=10
Ta=100°C
25
−25
VCE (sat) (V)
IC (mA)


IC – VBE
COMMON EMITTER
VCE=5V
Ta=100°C
25
−25
IC (A)
VBE (V)


SAFE OPERATING AREA
IC MAX. (PULSE)※
IC MAX. (CONTINUOUS)
10ms※
1ms※
100ms※
DC OPERATION
Ta=25°C
※ SINGLE NONREPETITIVE PULSE Ta=25°C
CURVES MUST BE DERATED LINEARLY WITH INCREASE IN TEMPERATURE
VCEO MAX.
IC (mA)
VCE (V)


PC – Ta
① MOUNTED ON CERAMIC SUBSTRATE (250mm²×0.8t)
②
PC (W)
Ta (°C)





H

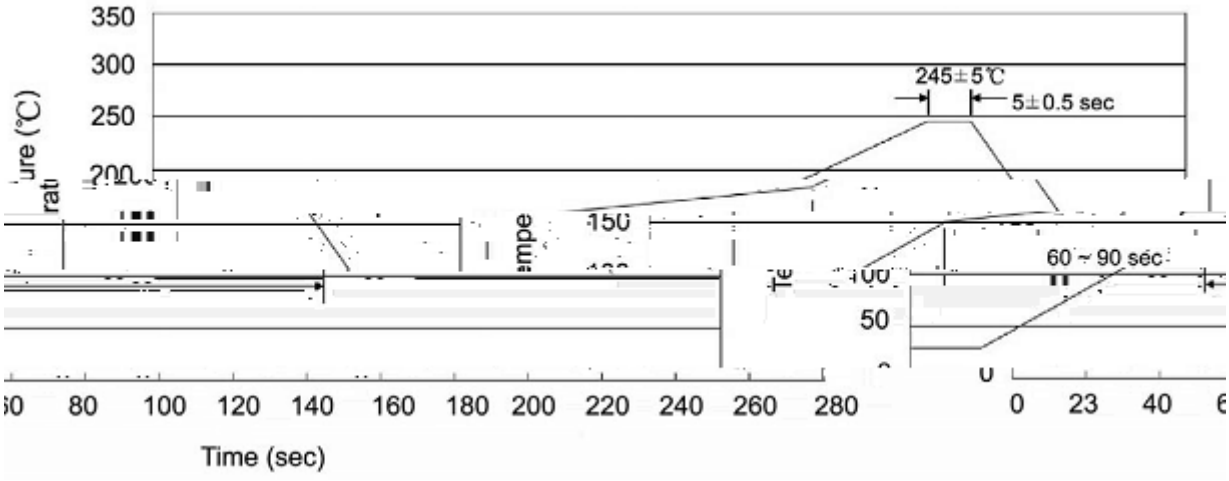
C

O

**

Note:

H: Company Code.




| | Note: |
|---|---|
| 1 25 150 60 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 245±5 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 2 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

ä 260±5 ä 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

| Package Type | Units | | | | | Dimension | | (unit mm$^3$) |
|---|---|---|---|---|---|---|---|---|
| | | | | | | | | |
| | | | | | | | | |